NSN 5962-01-420-9576

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View Online at https://aerobasegroup.com/nsn/5962-01-420-9576

Body Length:

0.358 inches

Body Width:

0.358 inches

Body Height:

0.100 inches

Maximum Power Dissipation Rating:

1.0 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

Pacer dawn

Features Provided:

Electrostatic sensitive and monolithic and programmed and 3-state output and bipolar

Inclosure Material:

Ceramic and glass

Inclosure Configuration:

Leadless flat pack

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

14 input

Criticality Code Justification:

Cbbl

Case Outline Source And Designator:

C-4 mil-m-38510

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit, programmed (prom 93z665a)

Voltage Rating And Type Per Characteristic:

-0.3 volts power source and 7.0 volts power source

Time Rating Per Chacteristic:

55.00 nanoseconds propagation delay time, high to low level output and 55.00 nanoseconds propagation delay time, low to high level output

Memory Device Type:

Programmed

Special Features:

Altered item, made from device 82009023x, cage 14933, microcircuit, memory, digital, bipolar 64k (8k x 8) prom, monolithic silicon

Test Data Document:

96906-mil-std883 standard (includes industry or association standards, individual manufactureer standards, etc.).

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| Terminal | Type And | Quantity: |
|------------|----------|-----------|
| 20 leadles | S | |

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A458a0